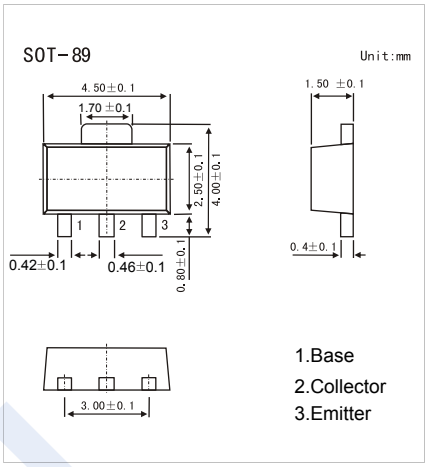
PNP Transistors

2SB1308



■ Features

- Power Transistor
- Excellent DC current Gain
- Low Collector-emitter Saturation Voltage

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-30	V
Collector - Emitter Voltage	V_{CEO}	-20	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-3	A
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 uA, I_E=0	-30			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-20			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 uA, I_C=0	-6			
Collector-base cut-off current	I_{CBO}	V_{CB}= -25V , I_E=0			-0.5	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-1.5 A, I_B=-150 mA			-0.45	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-1.5 A, I_B=-150 mA			-1.2	
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -500 mA	82		390	
Collector output capacitance	C_{ob}	V_{CB}= -20V, I_E= 0,f=1MHz		60		pF
Transition frequency	f_T	V_{CE}= -6V, I_C= -50 mA,f=30MHz		120		MHz

■ Classification of h_{fe}

Type	2SB1308-P	2SB1308-Q	2SB1308-R
Range	82-180	120-270	180-390
Marking	BF P*	BF Q*	BF R*

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■ Typical Characterisitics